



芯基达科技

MPVA8N65

Power MOSFET

SWITCHING REGULATOR APPLICATIONS

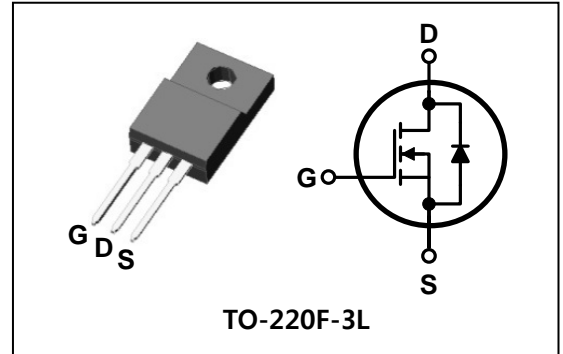
Features

- High Voltage : $BV_{DSS}=650V(\text{Min.})$
- Low C_{RSS} : $C_{RSS}=13.7pF(\text{Typ.})$
- Low gate charge : $Q_g=20nC(\text{Typ.})$
- Low $R_{DS(on)}$: $R_{DS(on)}=1.3\Omega(\text{Max.})$

Ordering Information

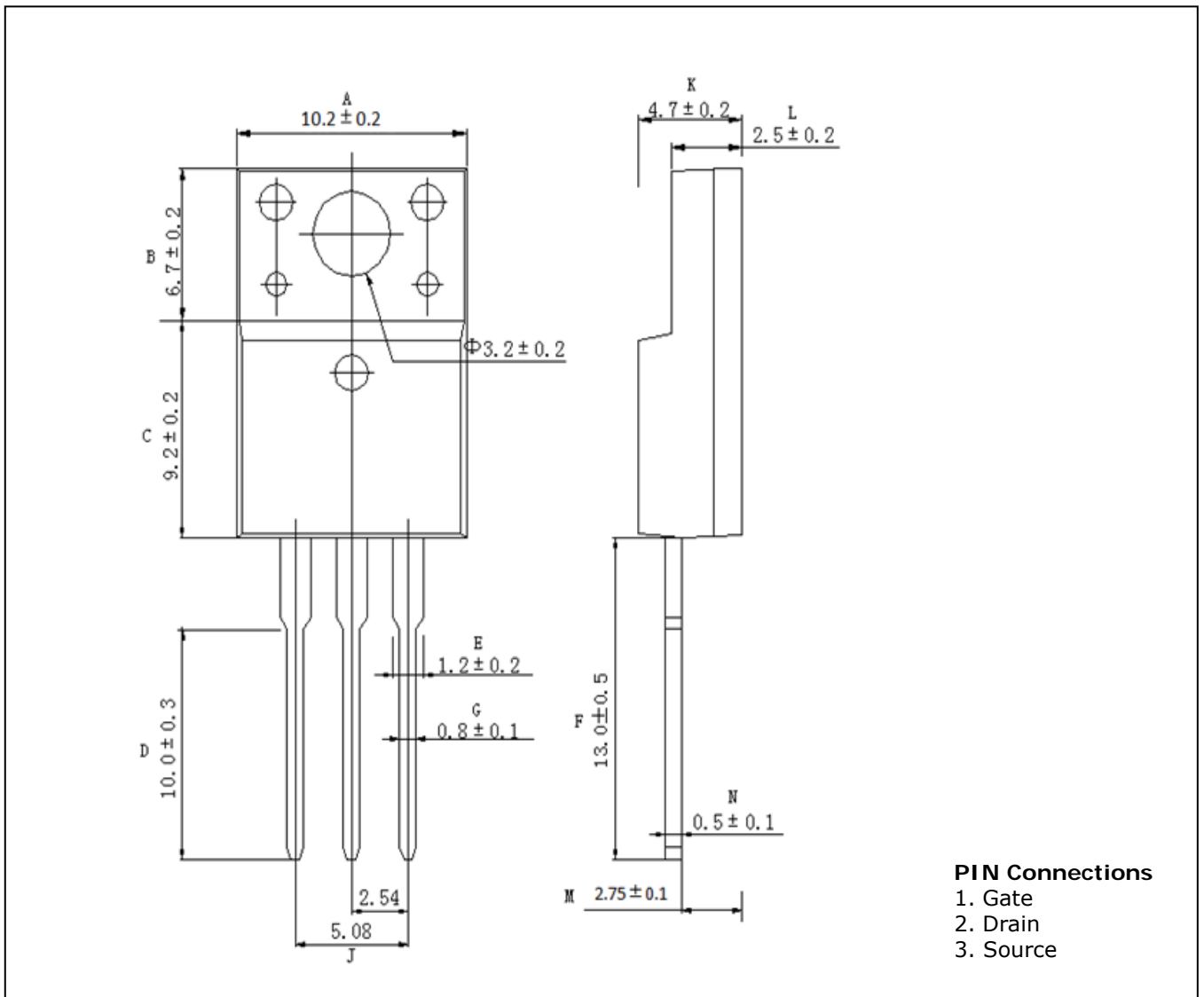
Type No.	Marking	Package Code
MPVA8N65	MPVA8N65	TO-220F-3L

PIN Connection



Outline Dimensions

unit : mm





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Absolute maximum ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Rating	Unit	
Drain-source voltage	V_{DSS}	650	V	
Gate-source voltage	V_{GSS}	± 30	V	
Drain current (DC) *	I_D	$T_C=25^\circ\text{C}$	8	A
		$T_C=100^\circ\text{C}$	4.8	A
Drain current (Pulsed) *	I_{DM}	32	A	
Power dissipation	P_D	40	W	
Avalanche current (Single) ②	I_{AS}	8	A	
Single pulsed avalanche energy ②	E_{AS}	266	mJ	
Avalanche current (Repetitive) ①	I_{AR}	8	A	
Repetitive avalanche energy ①	E_{AR}	11.6	mJ	
Junction temperature	T_J	150	$^\circ\text{C}$	
Storage temperature range	T_{stg}	-55~150		

* Limited by maximum junction temperature

Characteristic	Symbol	Typ.	Max.	Unit	
Thermal resistance	Junction-case	$R_{th(J-C)}$	-	3.1	$^\circ\text{C}/\text{W}$
	Junction-ambient	$R_{th(J-A)}$	-	62.5	



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Electrical Characteristics (T_C=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit	
Drain-source breakdown voltage	BV _{DSS}	I _D =250uA, V _{GS} =0V	650	-	-	V	
Gate threshold voltage	V _{GS(th)}	I _D =250uA, V _{DS} =V _{GS}	2.0	-	4.0	V	
Drain-source cut-off current	I _{DSS}	V _{DS} =700V, V _{GS} =0V	-	-	1	uA	
Gate leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±30V	-	-	±100	nA	
Drain-source on-resistance ④	R _{DS(on)}	V _{GS} =10V, I _D =4.0A		1.18	1.3	Ω	
Forward transfer conductance ④	g _{fs}	V _{DS} =10V, I _D =4.0A	-	11	-	S	
Input capacitance	C _{iss}	V _{GS} =0V, V _{DS} =25V f=1 MHz	-	2006	2507	pF	
Output capacitance	C _{oss}		-	148	185		
Reverse transfer capacitance	C _{rss}		-	13.7	17.1		
Turn-on delay time	t _{d(on)}	V _{DD} =300V, I _D =8A R _G =25Ω	-	23	-	ns	
Rise time	t _r		-	69	-		
Turn-off delay time	t _{d(off)}		③④	-	144		-
Fall time	t _f		-	77	-		
Total gate charge	Q _g	V _{DS} =560V, V _{GS} =10V I _D =8A	-	20	-	nC	
Gate-source charge	Q _{gs}		③④	-	4		-
Gate-drain charge	Q _{gd}		-	7.2	-		

Source-Drain Diode Ratings and Characteristics (T_C=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Source current (DC)	I _S	Integral reverse diode in the MOSFET	-	-	8	A
Source current (Pulsed) ①	I _{SM}		-	-	32	
Forward voltage ④	V _{SD}	V _{GS} =0V, I _S =8A	-	-	1.4	V
Reverse recovery time	t _{rr}	I _S =8A, V _{GS} =0V dI _F /dt=100A/us	-	420	-	ns
Reverse recovery charge	Q _{rr}		-	4.2	-	uC

Note ;

- ① Repetitive rating : Pulse width limited by maximum junction temperature
- ② L=7.74mH, I_{AS}=8A, V_{DD}=50V, R_G=25Ω, Starting T_J=25°C
- ③ Pulse Test : Pulse width≤300us, Duty cycle≤2%
- ④ Essentially independent of operating temperature

Fig. 11 Gate Charge Test Circuit & Waveform

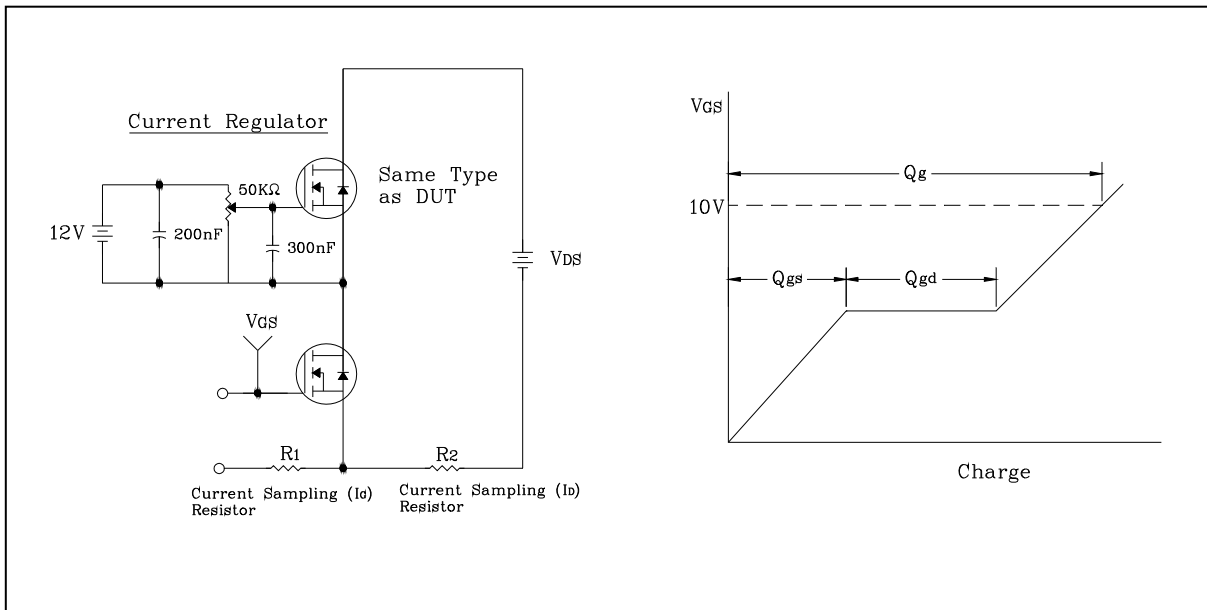


Fig. 12 Resistive Switching Test Circuit & Waveform

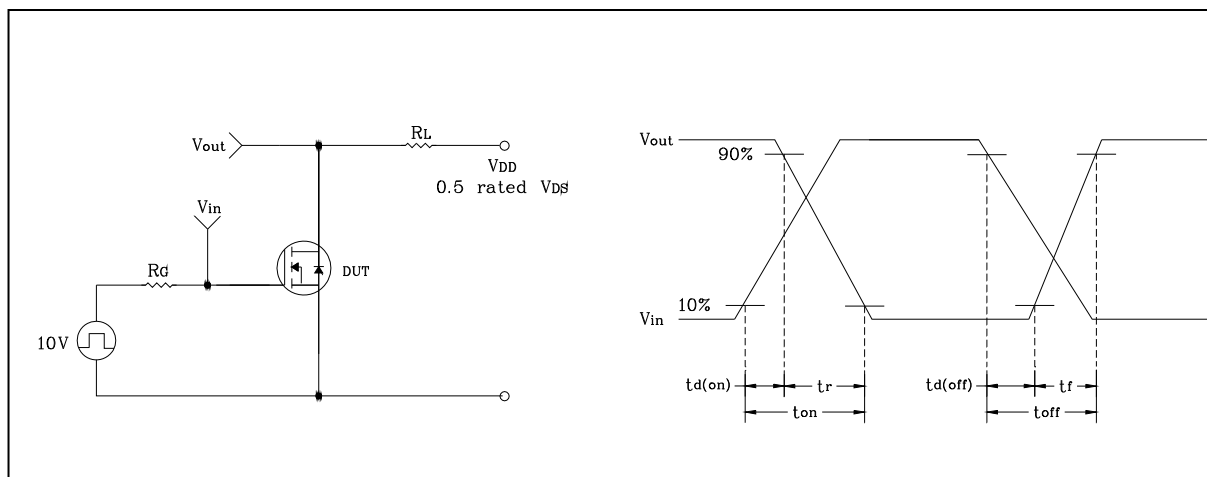


Fig. 13 E_{AS} Test Circuit & Waveform

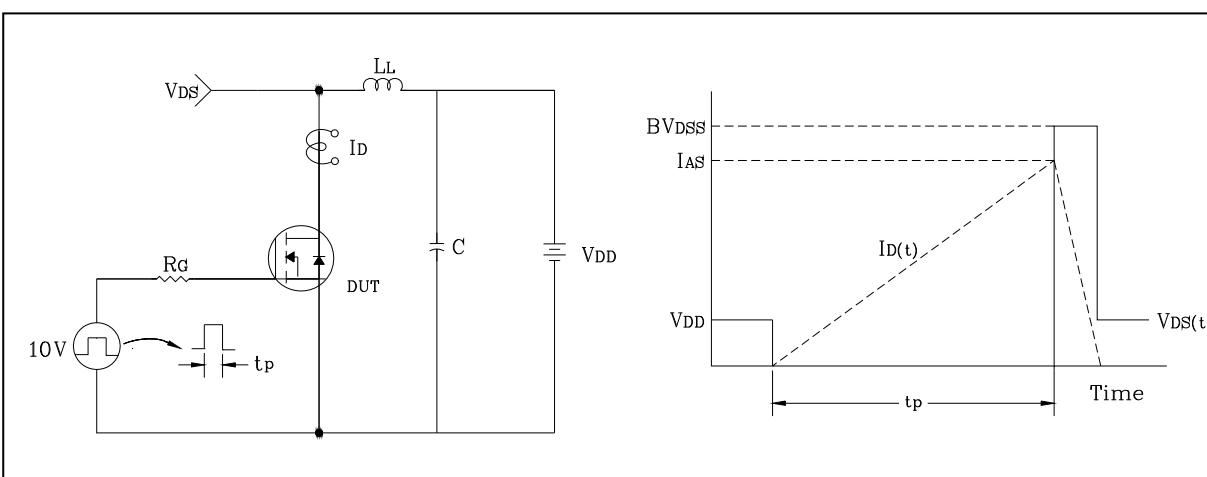


Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform

